

Medium Power Transistor

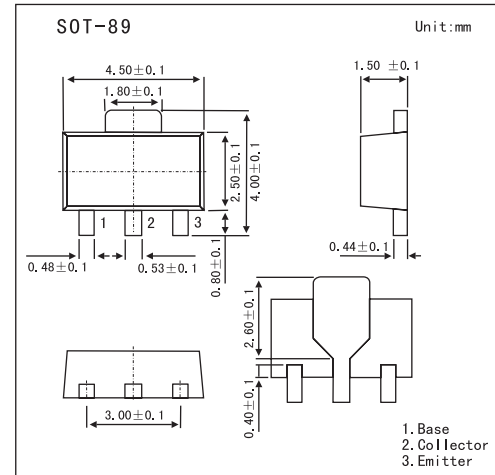
2SB1188

■ Features

- Low $V_{CE(sat)}$.

$V_{CE(sat)} = -0.5V$ (Typ.)

($I_C/I_B = -2A / -0.2A$)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base Voltage	V_{CBO}	-40	V
Collector-emitter Voltage	V_{CEO}	-32	V
Emitter-base Voltage	V_{EBO}	-5	V
Collector current	I_C	-2	A
	I_{CP}^*	-3	A
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* $PW=100ms$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C = -50 \mu A$	-40			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = -1mA$	-32			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -50 \mu A$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -20V$			-1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4V$			-1	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$		-0.5	-0.8	V
DC current transfer ratio	h_{FE}	$V_{CE} = -3V, I_C = -0.5A$	82		390	
Transition frequency	f_T	$V_{CE} = -5V, I_E = 0.5A, f = 30MHz$		100		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		50		pF

■ h_{FE} Classification

Marking	BC		
	P	Q	R
h_{FE}	82~180	120~270	180~390